

an active matrix circuit including at least one thin film transistor formed over a first surface of said insulating substrate;

a driving circuit including at least another one thin film transistor for driving the active matrix circuit formed over said first surface of the insulating substrate;

a counter substrate facing the first surface of said insulating substrate with a gap therebetween, said counter substrate covering said active matrix circuit and said driving circuit wherein said insulating substrate extends beyond at least one side edge of the counter substrate so as to provide an extended portion; and

at least one semiconductor integrated circuit chip disposed over said first surface of the extended portion of the insulating substrate and operationally connected with the driving circuit wherein said integrated circuit chip is at least one of a memory, an input port, a correction memory and a CPU.

wherein said at least one thin film transistor and said at least another one thin film transistor are formed from a common semiconductor film formed over the first surface of the insulating substrate.

7. (Amended) A display device comprising:

a substrate having a first surface;

an active matrix circuit including at least one thin film transistor formed over the first surface of the substrate;

a driving circuit including at least another one thin film transistor for driving the active matrix circuit formed over the first surface of the substrate; and

at least one semiconductor integrated circuit chip disposed over the first surface of the substrate and operationally connected to said driving circuit wherein said semiconductor integrated circuit chip is at least one of a memory, an input port, [a memory] and a CPU

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(concluded)

wherein said at least one thin film transistor and said at least another one thin film transistor are formed from a common semiconductor film formed over the first surface of the substrate, and

wherein said at least one thin film transistor of the active matrix circuit has at least one lightly doped drain between a channel region and a drain region thereof.

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17. (Amended) An electric device comprising:

a substrate having an insulating surface;

a plurality of thin film transistors formed on the insulating surface, said plurality of thin film transistors being formed from a common semiconductor film formed on said insulating surface; and

at least one single crystalline semiconductor integrated circuit chip formed on the insulating surface wherein said semiconductor integrated circuit chip is at least one of a memory, an input port, a correction memory and a CPU;

wherein at least one of the thin film transistors is provided as an active matrix circuit, at least another one of the thin film transistors is provided as at least one driving circuit for driving the active matrix circuit and the semiconductor integrated circuit chip is provided as a control circuit for controlling the driving circuit, and wherein said common semiconductor film is formed by crystallizing a semiconductor film comprising amorphous silicon deposited on said insulating surface.

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21. (Amended) An electric device comprising:

a first substrate;

an active matrix circuit formed over said first substrate with at least one thin film transistor;

a driving circuit formed over said first substrate with at least one other thin film transistor for driving the active matrix circuit;

a second substrate facing said first substrate with a gap therebetween, said first substrate extending beyond at least one side edge of the second substrate to provide an extended portion wherein said second substrate covers said active matrix circuit and said driving circuit; and

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(concluded)

a semiconductor integrated circuit chip disposed over the extended portion of said first substrate and operationally connected to said driving circuit wherein said integrated circuit chip is at least one of a memory, an input port, a correction memory and a CPU,

wherein said at least one thin film transistor and said one other thin film transistor are formed from a common semiconductor film obtained by crystallizing a semiconductor film comprising amorphous silicon deposited over said first substrate.

33. (Amended) A [liquid crystal] display device according to claim 32 wherein said semiconductor film comprises crystalline silicon.

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34. (Amended) A [liquid crystal] display device according to claim 32 wherein said semiconductor integrated circuit chip is a memory.

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35. (Amended) A [liquid crystal] display device according to claim 32 wherein said semiconductor integrated circuit chip is a CPU.

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41. (Amended) The device according to claim [38] 21 further comprising a liquid crystal material disposed between said first and second substrates.

REMARKS

The Examiner's Official Action dated September 1, 1999 has been received and its contents carefully noted. Filed concurrently herewith is a *Request for a Two Month Extension of Time* which extends the shortened statutory period for response to February